ROHS

HALOGEN

FREE



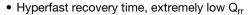
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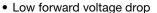
Hyperfast Rectifier, 8 A FRED Pt®



PRIMARY CHARACTERISTICS								
I _{F(AV)}	8 A							
V_{R}	600 V							
V _F at I _F	1.5 V							
t _{rr} (typ.)	14 ns							
T _J max.	175 °C							
Package	2L TO-220AC							
Circuit configuration	Single							

FEATURES





• 175 °C operating junction temperature

• Low leakage current

• True 2 pin package

- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		600	V
Average rectified forward current in DC	I _{F(AV)}	T _C = 142 °C	8	۸
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80	А
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-	.,			
Forward voltage	V _F	I _F = 8 A	-	2.5	3.4	V			
		I _F = 8 A, T _J = 150 °C	-	1.5	2.0				
Poverse leakage current	I _R	$V_R = V_R$ rated	-	0.02	30				
Reverse leakage current		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	21	150	μA			
Junction capacitance	C _T	V _R = 600 V	-	6	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH			



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 A, dI_F/dt = 10$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$			18			
Payaraa raaayany tima		I _F = 8 A, dI _F /dt = 10	I _F = 8 A, dI _F /dt = 100 A/μs, V _R = 30 V			24	no		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	17	-	ns		
		T _J = 125 °C	$I_F = 8 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_B = 390 \text{ V}$	-	33	-			
Deal, marriage and a second	1	T _J = 25 °C		-	2.6	-	A nC		
Peak recovery current	I _{RRM}	T _J = 125 °C		-	4.3	-			
Poverse receivery charge	0	T _J = 25 °C] "	-	22	-			
Reverse recovery charge	Q_{rr}	T _J = 125 °C		-	77	-			
Reverse recovery time	t _{rr}		I _F = 8 A,	-	26	-	ns		
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 600 A/\mu s$,	-	11	-	Α		
Reverse recovery charge	Q _{rr}	1	V _R = 390 V		150	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance,	R _{thJC}		-	2.0	2.6				
junction-to-case	PthJC		-	4.6	5.5				
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W			
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Maight			-	2	-	g			
Weight			-	0.07	-	OZ.			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style 2L TO-220AC	ETX0806						



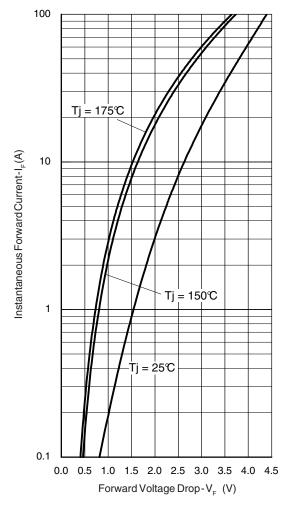


Fig. 1 - Typical Forward Voltage Drop Characteristics

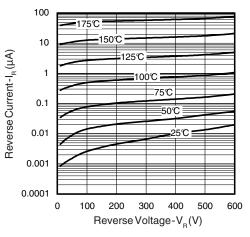


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

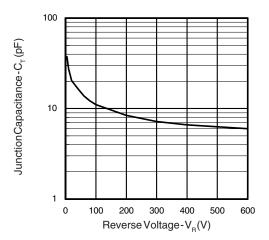


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

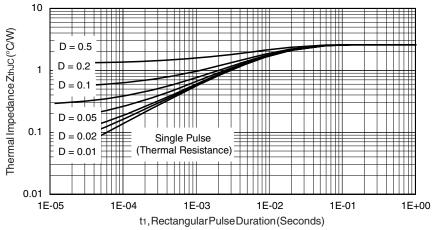


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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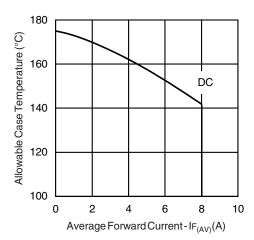


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

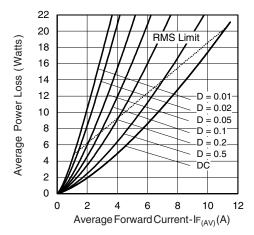


Fig. 6 - Forward Power Loss Characteristics

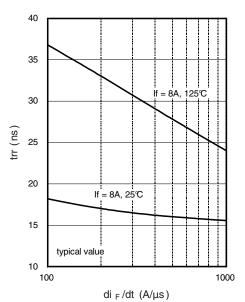


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

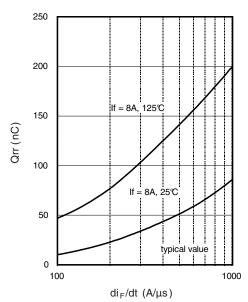
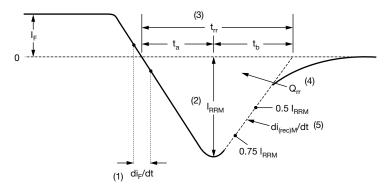


Fig. 8 - Typical Stored Charge vs. dl_F/dt



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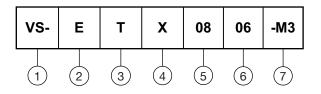


- (1) di_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (5) di_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Circuit configuration:

E = single

- 3 T = 2L TO-220AC
- 4 X = hyperfast recovery time
- 5 Current code: 08 = 8 A
- 6 Voltage code: 06 = 600 V
- 7 Environmental digit:
 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-ETX0806-M3	50	1000	Antistatic plastic tube						

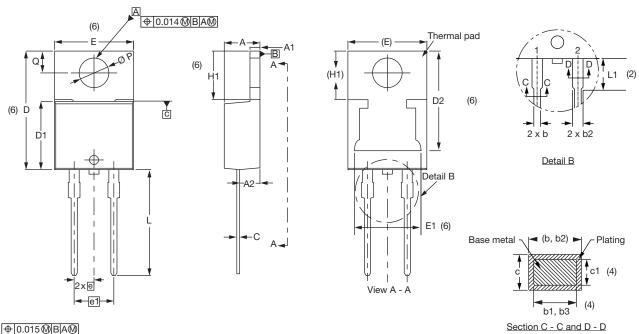
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96156						
Part marking information	www.vishay.com/doc?95391						

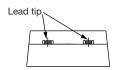


Vishay Semiconductors

2L TO-220AC

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AC

SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355				•	•			

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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